

/ Descriptions

SOT-23 N MOS - CHANNEL MOSFET in a SOT-23 Plastic Package.

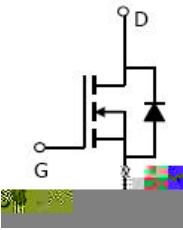
/ Features

$V_{DS} (V) = 30V$
 $I_D = 5.8 A (V_{GS} = 10V)$
 $R_{DS(ON)} < 28m (V_{GS} = 10V)$
 $R_{DS(ON)} < 33m (V_{GS} = 4.5V)$
 $R_{DS(ON)} < 52m (V_{GS} = 2.5V)$
 无卤产品。 HF Product.

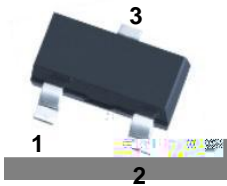
/ Applications

This device is suitable for use as a load switch or in PWM applications.

/ Equivalent Circuit



/ Pinning



PIN1 G PIN 2 S PIN 3 D

/ Marking

Marking	A0H
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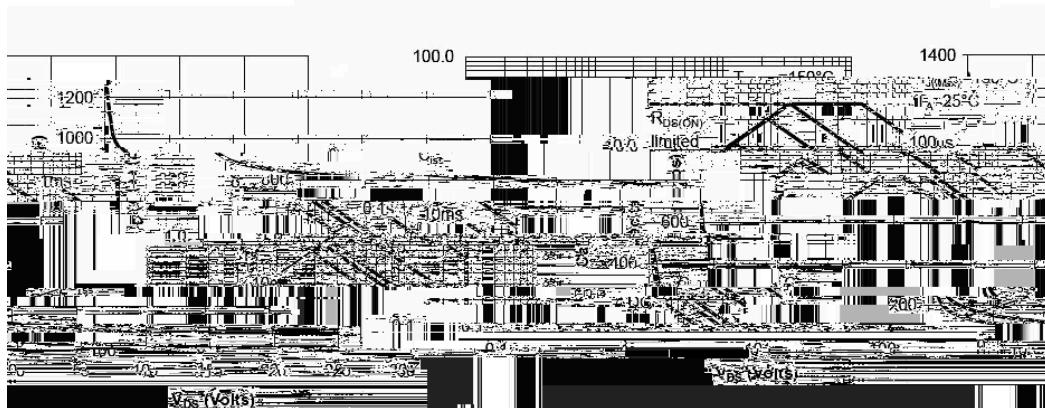
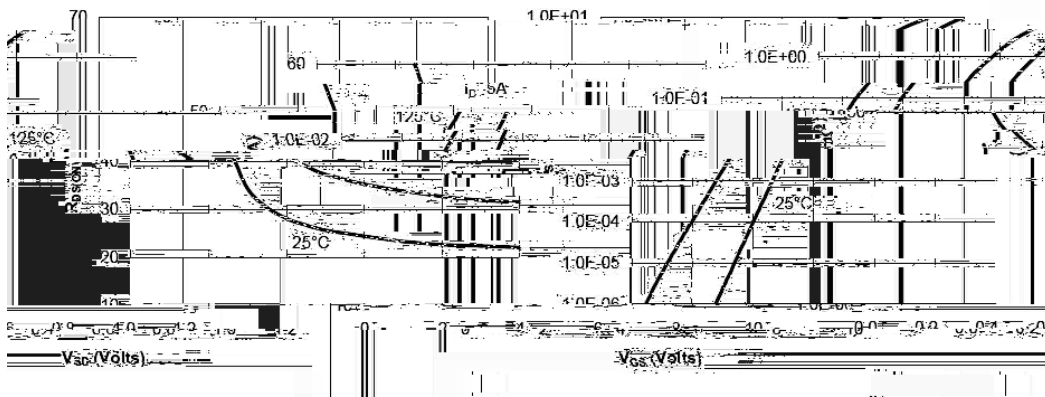
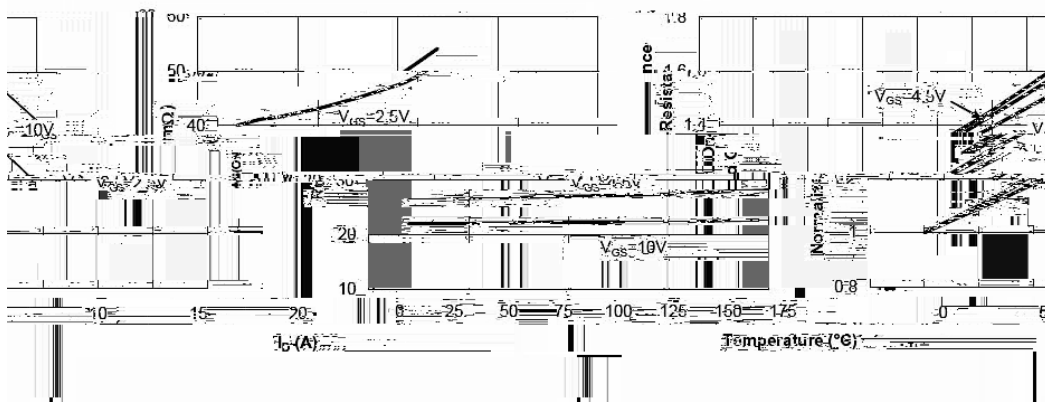
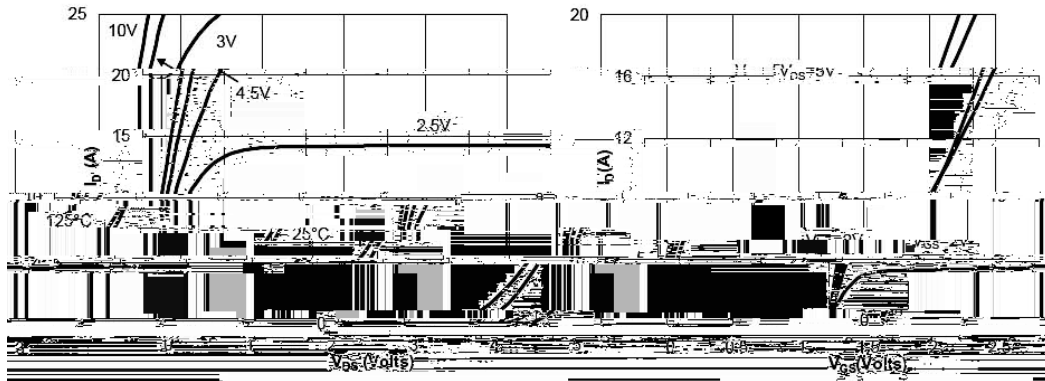


/ Electrical Characteristics(Ta=25)

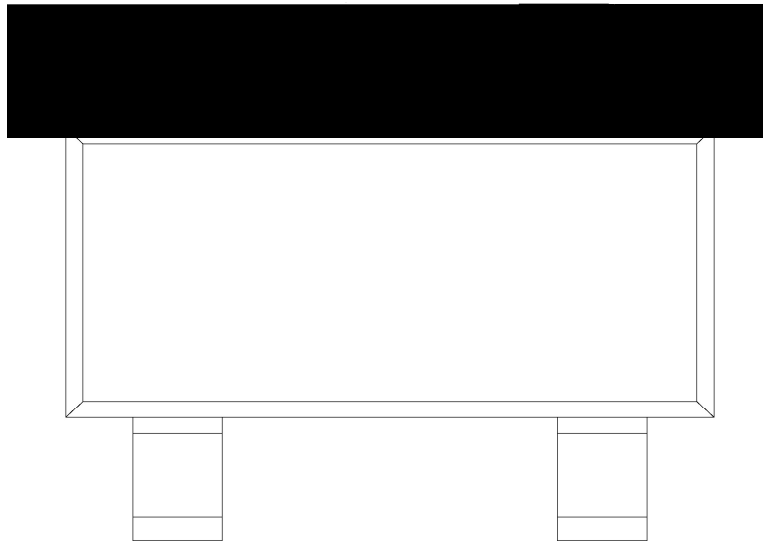
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Capacitance	C_{iss}	$V_{DS}=15V$ $V_{GS}=0V$ $f=1MHz$		823	1030	pF
Output Capacitance	C_{oss}			99		
Reverse Transfer Capacitance	C_{rss}			77		
Gate resistance	R_g	$V_{GS}=0V$ $V_{DS}=0V,$ $f=1MHz$		1.2	3.6	
Total Gate Charge	Q_g	$V_{GS}=4.5V,$ $V_{DS}=15V,$ $I_D=5.8A$		9.7	12	nC
Gate Source Charge	Q_{gs}			1.6		
Gate Drain Charge	Q_{gd}			3.1		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $R_L=2.7$ $V_{DS}=15V$ $R_{GEN}=3$		3.3	5	ns
Turn-On Rise Time	t_r			4.8	7	
Turn-Off Delay Time	$t_{d(off)}$			26.3	40	
Turn-Off Fall Time	t_f			4.1	6	
Body Diode Reverse Recovery Time	t_{rr}	$I_F=5A$ $di/dt=100A/\mu s$		16	20	ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F=5A$ $di/dt=100A/\mu s$		8.9	12	nC



/ Electrical Characteristic Curve



/ Marking Instructions



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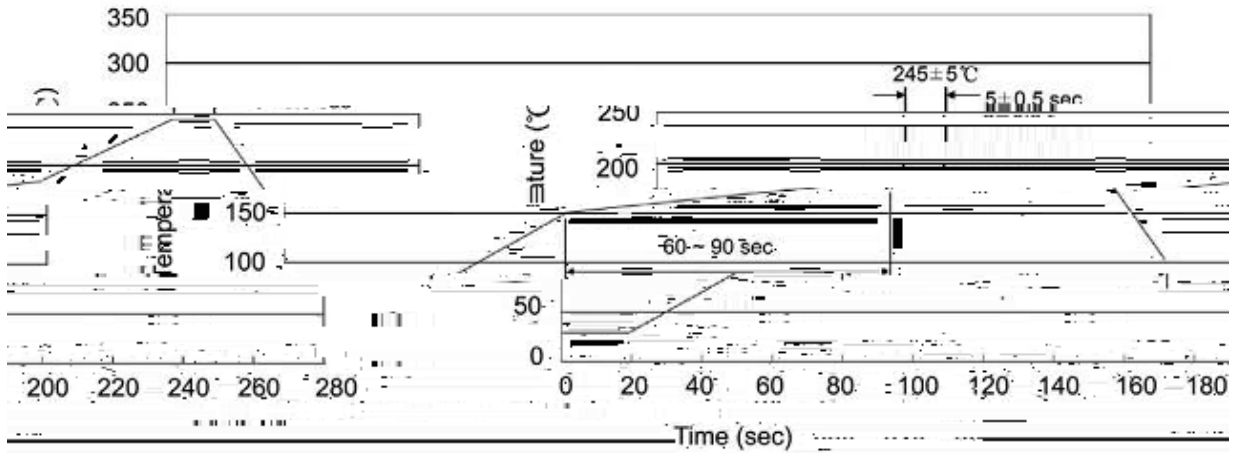
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Note:

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() / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

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|---|-------|-----|-------|----------|---|
| 1 | 150 | 180 | 60 | 90sec; | 1.Preheating:150~180 , Time:60~90sec. |
| 2 | 245±5 | | 5±0.5 | sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type
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